

L Number	Hits	Search Text	DB	Time stamp
23	1993	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.	USPAT; US-PGPUB	2003/05/01 15:26
24	211	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (clean with air)	USPAT; US-PGPUB	2003/05/01 15:27
25	42	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (clean with air) and tokyo.as.	USPAT; US-PGPUB	2003/05/01 15:27
31	0	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (edge with exposure with (above below under underneath over ) with (thermal\$4))	USPAT; US-PGPUB; JPO; DERWENT	2003/05/01 16:14
32	5	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (edge with exposure with unit) same (heat\$3 cool\$3)	USPAT; US-PGPUB; JPO; DERWENT	2003/05/01 16:18
33	42	(edge with exposure with unit) same (heat\$3 cool\$3)	USPAT; US-PGPUB	2003/05/01 16:19
-	1244	(118/719).CCLS.	USPAT; US-PGPUB	2003/04/29 11:57
-	241	((156/345.31) or (156/345.32)).CCLS.	USPAT; US-PGPUB	2003/04/29 11:15
-	1	2000-265318	JPO; DERWENT	2003/04/29 11:20
-	912	((414/935) or (414/937) or (414/938)).CCLS.	USPAT; US-PGPUB	2003/04/29 11:57
-	785	((414/935) or (414/937) or (414/938)).CCLS.) not ((118/719).CCLS.) ((156/345.31) or (156/345.32)).CCLS.)) ("9 and applied.as.").PN.	USPAT; US-PGPUB	2003/05/01 17:03
-	0		USPAT; US-PGPUB	2003/05/01 17:03
-	1245	(118/719).CCLS.	USPAT; US-PGPUB	2003/04/29 15:38
-	86	((118/719).CCLS.) and applied.as.	USPAT; US-PGPUB	2003/04/29 15:39
-	1749	(process\$3 with (chamber unit section apparatus) with (above below under over) with (transfer\$4 transport\$3)) same (substrate wafer semiconductor)	USPAT; US-PGPUB	2003/04/30 16:10
-	200	(process\$3 with (chamber unit section apparatus) with (above below under over) with (transfer\$4 transport\$3)) same (substrate wafer semiconductor)	EPO; JPO; DERWENT	2003/04/30 16:38
-	28	(process\$3 with (chamber unit section apparatus) with (above below under over) with (transfer\$4 transport\$3) with (locat\$3 arrang\$3)) same (substrate wafer semiconductor)	EPO; JPO; DERWENT	2003/04/30 16:42
-	189	(process\$3 with (chamber unit section apparatus) with (above below under over) with (transfer\$4 transport\$3) with (locat\$3 arrang\$3)) same (substrate wafer semiconductor)	USPAT; US-PGPUB	2003/04/30 16:50

-	11	((US-6503365-\$ or US-6473151-\$ or US-6391114-\$ or US-6377329-\$ or US-6328768-\$ or US-6270619-\$ or US-6251191-\$ or US-6235171-\$ or US-6183564-\$ or US-6168667-\$ or US-5963753-\$ or US-5820679-\$ or US-5769952-\$ or US-5695564-\$ or US-5417537-\$ or US-5405230-\$ or US-5286296-\$ or US-4981408-\$ or US-4927484-\$ or US-6467491-\$ or US-6051101-\$ or US-5788868-\$ or US-6511315-\$ or US-6464789-\$ or US-6299363-\$ or US-6253118-\$).did. or (US-6099643-\$ or US-6024502-\$ or US-5937223-\$ or US-5733024-\$ or US-5639301-\$ or US-5626675-\$ or US-5571325-\$ or US-5544421-\$ or US-5430271-\$ or US-5061144-\$ or US-4787800-\$ or US-6322119-\$ or US-6264705-\$ or US-4985722-\$ or US-6402400-\$ or US-5826129-\$ or US-6402401-\$ or US-6341903-\$ or US-6293713-\$ or US-6290405-\$ or US-6264381-\$ or US-6074154-\$ or US-6215545-\$ or US-5803932-\$ or US-5664254-\$ or US-5442416-\$ or US-5202716-\$).did. or (US-5766824-\$ or US-5651823-\$ or US-6515731-\$ or US-6267516-\$ or US-6002108-\$ or US-5915396-\$ or US-6544338-\$ or US-6245156-\$ or US-5668733-\$ or US-5725664-\$ or US-5942013-\$ or US-5974682-\$ or US-6379056-\$ or US-6224274-\$).did. or (US-20020197878-\$ or US-2001008174-\$ or US-20030019578-\$ or US-20020189758-\$ or US-20020137346-\$ or US-20020092368-\$).did. or (JP-2002184706-\$).did. or (EP-1184895-\$).did.) and inspect\$3 ((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.	USPAT; US-PGPUB	2003/05/01 17:03
-	1993	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.	USPAT; US-PGPUB	2003/05/01 15:26
-	2	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (inspect\$3 with (thermal\$3 heat\$3) with unit)	USPAT; US-PGPUB	2003/05/01 11:18
-	10	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (inspect\$3 with (thermal\$3 heat\$3))	USPAT; US-PGPUB	2003/05/01 11:29
-	7	((118/719) or (156/345.31) or (156/345.32) or (414/939) or (414/935)).CCLS.) and (inspect\$3 with (plural\$ mulitip\$5) with (chamber unit))	USPAT; US-PGPUB	2003/05/01 11:33
-	29	((semiconductor wafer substrate) with inspect\$3 with (plural\$ mulitip\$5) with (chamber unit)) same (transfer\$4 transport\$3)	USPAT; US-PGPUB	2003/05/01 11:35